

## EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	1	10/612414	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/07 17:39
L4	14	("20020179908"   "20030124778"   "20030151049"   "20030170938"   "5563440"   "6306693"   "6362030"   "6462723"   "6506642"   "6528852"   "6635505"   "6646288"   "6706544"   "6781646").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2007/01/07 17:42
L5	290	(gate adj electrode) near10 between near10 (first near gate near (dielectric or insulating) near (film or layer))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/07 17:43
L6	109	(gate adj electrode) near10 between near10 (first near gate near (dielectric or insulating) near (film or layer)) near10 (second near gate near (dielectric or insulating) near (film or layer))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/07 17:44
L7	7	(gate adj electrode) near10 between near10 (first near gate near (dielectric or insulating) near (film or layer)) near10 (second near gate near (dielectric or insulating) near (film or layer)) same (tft or (thin near film near transistor))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/07 17:45
L8	7	(gate adj electrode) near10 between near10 (first near gate near (dielectric or insulating or insulation or oxide) near (film or layer)) near10 (second near gate near (dielectric or insulating) near (film or layer)) same (tft or (thin near film near transistor))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/07 17:45
L9	10	(gate adj electrode) near10 between near10 (first near gate near (dielectric or insulating or insulation or oxide) near (film or layer)) near10 (second near gate near (dielectric or insulating or insulation or oxide) near (film or layer)) same (tft or (thin near film near transistor))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/07 17:46

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L10	153	(gate adj electrode) near10 between near10 (first near gate near (dielectric or insulating or insulation or oxide) near (film or layer)) near10 (second near gate near (dielectric or insulating or insulation or oxide) near (film or layer))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/07 17:47
L11	994	(gate adj electrode) near10 (first near gate near (dielectric or insulating or insulation or oxide) near (film or layer)) near10 (second near gate near (dielectric or insulating or insulation or oxide) near (film or layer))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/07 17:47
L12	207	(gate adj electrode) near10 (first near gate near (dielectric or insulating or insulation or oxide) near (film or layer)) near10 (second near gate near (dielectric or insulating or insulation or oxide) near (film or layer)) and (tft or (thin near film near transistor))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/07 17:50
L13	13	(gate adj electrode) near10 (first near gate near (dielectric or insulating or insulation or oxide) near (film or layer)) near10 (second near gate near (dielectric or insulating or insulation or oxide) near (film or layer)) and (tft or (thin near film near transistor)) and ((four or fourth) near (tft or (thin near film near transistor)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/07 17:52
L14	5	(gate adj electrode) near10 (first near gate near (dielectric or insulating or insulation or oxide) near (film or layer)) near10 (second near gate near (dielectric or insulating or insulation or oxide) near (film or layer)) and (tft or (thin near film near transistor)) and ((four or fourth) adj (tft or (thin near film near transistor)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/07 17:52
L15	671	((four or fourth) adj (tft or (thin near film near transistor)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/07 17:53

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L16	302	((four or fourth) adj (tft or (thin near film near transistor))) and ((three or third) adj (tft or (thin near film near transistor)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/07 17:54
L17	159	((four or fourth) adj (tft or (thin near film near transistor))) and ((three or third) adj (tft or (thin near film near transistor))) and (gate adj electrode) and (gate adj (insulating or dielectric or insulation or oxide))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/07 17:54
L18	96	((four or fourth) adj (tft or (thin near film near transistor))) and ((three or third) adj (tft or (thin near film near transistor))) and (gate adj electrode) and (gate adj (insulating or dielectric or insulation or oxide)) and ((silicon or semiconductor or active or silicon) near (layer or film))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/07 17:57
L19	10487	(gate adj electrode) near10 between near10 (gate adj (insulating or dielectric or insulation or oxide))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/07 17:57
L20	1349	(gate adj electrode) near10 between near10 (gate adj (insulating or dielectric or insulation or oxide)) same (tft or (thin near film near transistor))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/07 17:57
L21	171	(gate adj electrode) near2 between near2 (gate adj (insulating or dielectric or insulation or oxide)) same (tft or (thin near film near transistor))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/07 17:58
L22	5	(gate adj electrode) near2 between near2 ((first or second or upper or lower or top or bottom) near gate adj (insulating or dielectric or insulation or oxide)) same (tft or (thin near film near transistor))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/07 17:58
L23	5	(gate adj electrode) near2 between near2 ((first or second or upper or lower or top or bottom) adj gate adj (insulating or dielectric or insulation or oxide)) same (tft or (thin near film near transistor))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/07 18:00

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L24	335	(gate adj electrode) near5 ((first or second or upper or lower or top or bottom) adj gate adj (insulating or dielectric or insulation or oxide)) same (tft or (thin near film near transistor))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/07 18:00
L25	159	((first or second or upper or lower or top or bottom or third) adj gate adj electrode) near5 ((first or second or upper or lower or top or bottom) adj gate adj (insulating or dielectric or insulation or oxide)) same (tft or (thin near film near transistor))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/07 18:03
L26	14	"6225150".pn. or "5055899".pn. or "5166085".pn. or "5877514".pn. or "5969377".pn. or "6225644".pn. or "5396084".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/07 18:04